

Automotive N- and P-Channel 100 V (D-S) 175 °C MOSFET

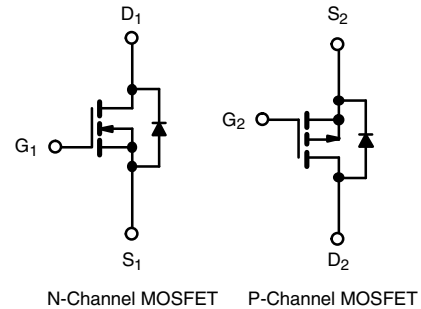
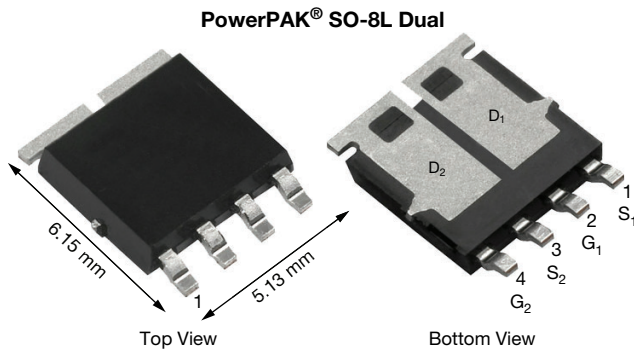
 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE

| PRODUCT SUMMARY | | |
|---|---------------------|-----------|
| | N-CHANNEL | P-CHANNEL |
| V_{DS} (V) | 100 | -100 |
| $R_{DS(on)}$ (Ω) at $V_{GS} = \pm 10$ V | 0.0450 | 0.1460 |
| $R_{DS(on)}$ (Ω) at $V_{GS} = \pm 4.5$ V | 0.0580 | 0.2065 |
| I_D (A) | 15 | -9.5 |
| Configuration | N- and P-Pair | |
| Package | PowerPAK SO-8L Dual | |

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_G and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



| ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted) | | | | |
|---|----------------|----------------|-----------------|------|
| PARAMETER | SYMBOL | N-CHANNEL | P-CHANNEL | UNIT |
| Drain-Source Voltage | V_{DS} | 100 | -100 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | | |
| Continuous Drain Current | I_D | $T_C = 25$ °C | 15 ^a | A |
| | | $T_C = 125$ °C | 9.6 | |
| Continuous Source Current (Diode conduction) ^a | I_S | 15 | -15 | A |
| Pulsed Drain Current ^b | I_{DM} | 40 | -21 | |
| Single Pulse Avalanche Current | I_{AS} | 13 | -6 | |
| Single Pulse Avalanche Energy | E_{AS} | L = 0.1 mH | 8.4 | mJ |
| Maximum Power Dissipation ^b | | | $T_C = 25$ °C | |
| | | $T_C = 125$ °C | 9 | 9 |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +175 | | °C |
| Soldering Recommendations (Peak temperature) ^{d, e} | | 260 | | |

| THERMAL RESISTANCE RATINGS | | | | |
|----------------------------|------------|-----------|-----------|------|
| PARAMETER | SYMBOL | N-CHANNEL | P-CHANNEL | UNIT |
| Junction-to-Ambient | R_{thJA} | 85 | 85 | °C/W |
| Junction-to-Case (Drain) | | | | |

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



| SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | | |
|--|--------------|---|---|------|------|-----------|--------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | N-Ch | 100 | - | - | V |
| | | $V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$ | P-Ch | -100 | - | - | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | N-Ch | 1.5 | 2 | 2.5 | V |
| | | $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$ | P-Ch | -1.5 | -2 | -2.5 | |
| Gate-Source Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | N-Ch | - | - | ± 100 | nA |
| | | | P-Ch | - | - | ± 100 | |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{GS} = 0\text{ V}$ | $V_{DS} = 100\text{ V}$ | N-Ch | - | - | 1 |
| | | $V_{GS} = 0\text{ V}$ | $V_{DS} = -100\text{ V}$ | P-Ch | - | - | -1 |
| | | $V_{GS} = 0\text{ V}$ | $V_{DS} = 100\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | N-Ch | - | - | 50 |
| | | $V_{GS} = 0\text{ V}$ | $V_{DS} = -100\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | P-Ch | - | - | -50 |
| | | $V_{GS} = 0\text{ V}$ | $V_{DS} = 100\text{ V}, T_J = 175\text{ }^\circ\text{C}$ | N-Ch | - | - | 150 |
| | | $V_{GS} = 0\text{ V}$ | $V_{DS} = -100\text{ V}, T_J = 175\text{ }^\circ\text{C}$ | P-Ch | - | - | -150 |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{GS} = 10\text{ V}$ | $V_{DS} \geq 5\text{ V}$ | N-Ch | 10 | - | A |
| | | $V_{GS} = -10\text{ V}$ | $V_{DS} \leq 5\text{ V}$ | P-Ch | -6 | - | - |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$ | $I_D = 6\text{ A}$ | N-Ch | - | 0.0365 | 0.0450 |
| | | $V_{GS} = -10\text{ V}$ | $I_D = -6\text{ A}$ | P-Ch | - | 0.1184 | 0.1460 |
| | | $V_{GS} = 10\text{ V}$ | $I_D = 6\text{ A}, T_J = 125\text{ }^\circ\text{C}$ | N-Ch | - | - | 0.0774 |
| | | $V_{GS} = -10\text{ V}$ | $I_D = -6\text{ A}, T_J = 125\text{ }^\circ\text{C}$ | P-Ch | - | - | 0.2435 |
| | | $V_{GS} = 10\text{ V}$ | $I_D = 6\text{ A}, T_J = 175\text{ }^\circ\text{C}$ | N-Ch | - | - | 0.0978 |
| | | $V_{GS} = -10\text{ V}$ | $I_D = -6\text{ A}, T_J = 175\text{ }^\circ\text{C}$ | P-Ch | - | - | 0.2994 |
| | | $V_{GS} = 4.5\text{ V}$ | $I_D = 4\text{ A}$ | N-Ch | - | 0.0468 | 0.0580 |
| | | $V_{GS} = -4.5\text{ V}$ | $I_D = -4\text{ A}$ | P-Ch | - | 0.1669 | 0.2065 |
| Forward Transconductance ^b | g_{fs} | $V_{DS} = 15\text{ V}, I_D = 6\text{ A}$ | N-Ch | - | 15 | - | S |
| | | $V_{DS} = -15\text{ V}, I_D = -6\text{ A}$ | P-Ch | - | 7 | - | |
| Dynamic ^b | | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}$ | $V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | N-Ch | - | 420 | 600 |
| | | $V_{GS} = 0\text{ V}$ | $V_{DS} = -25\text{ V}, f = 1\text{ MHz}$ | P-Ch | - | 480 | 650 |
| Output Capacitance | C_{oss} | $V_{GS} = 0\text{ V}$ | $V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | N-Ch | - | 260 | 350 |
| | | $V_{GS} = 0\text{ V}$ | $V_{DS} = -25\text{ V}, f = 1\text{ MHz}$ | P-Ch | - | 250 | 350 |
| Reverse Transfer Capacitance | C_{rss} | $V_{GS} = 0\text{ V}$ | $V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | N-Ch | - | 17 | 25 |
| | | $V_{GS} = 0\text{ V}$ | $V_{DS} = -25\text{ V}, f = 1\text{ MHz}$ | P-Ch | - | 20 | 30 |
| Total Gate Charge ^c | Q_g | $V_{GS} = 10\text{ V}$ | $V_{DS} = 50\text{ V}, I_D = 1\text{ A}$ | N-Ch | - | 9 | 15 |
| | | $V_{GS} = -10\text{ V}$ | $V_{DS} = -50\text{ V}, I_D = -1\text{ A}$ | P-Ch | - | 12 | 20 |
| Gate-Source Charge ^c | Q_{gs} | $V_{GS} = 10\text{ V}$ | $V_{DS} = 50\text{ V}, I_D = 1\text{ A}$ | N-Ch | - | 1.2 | - |
| | | $V_{GS} = -10\text{ V}$ | $V_{DS} = -50\text{ V}, I_D = -1\text{ A}$ | P-Ch | - | 2 | - |
| Gate-Drain Charge ^c | Q_{gd} | $V_{GS} = 10\text{ V}$ | $V_{DS} = 50\text{ V}, I_D = 1\text{ A}$ | N-Ch | - | 1.9 | - |
| | | $V_{GS} = -10\text{ V}$ | $V_{DS} = -50\text{ V}, I_D = -1\text{ A}$ | P-Ch | - | 3 | - |
| Gate Resistance | R_g | $f = 1\text{ MHz}$ | | N-Ch | 1.3 | 2.7 | 4.5 |
| | | | | P-Ch | 5 | 10.2 | 15.5 |
| Turn-On Delay Time ^c | $t_{d(on)}$ | $V_{DD} = 50\text{ V}, R_L = 50\text{ }\Omega, I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 5\text{ }\Omega$ | | N-Ch | - | 8 | 15 |
| | | $V_{DD} = -50\text{ V}, R_L = 50\text{ }\Omega, I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 5\text{ }\Omega$ | | P-Ch | - | 12 | 20 |
| Rise Time ^c | t_r | $V_{DD} = 50\text{ V}, R_L = 50\text{ }\Omega, I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 5\text{ }\Omega$ | | N-Ch | - | 4 | 10 |
| | | $V_{DD} = -50\text{ V}, R_L = 50\text{ }\Omega, I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 5\text{ }\Omega$ | | P-Ch | - | 5 | 10 |
| Turn-Off Delay Time ^c | $t_{d(off)}$ | $V_{DD} = 50\text{ V}, R_L = 50\text{ }\Omega, I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 5\text{ }\Omega$ | | N-Ch | - | 20 | 35 |
| | | $V_{DD} = -50\text{ V}, R_L = 50\text{ }\Omega, I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 5\text{ }\Omega$ | | P-Ch | - | 30 | 50 |
| Fall Time ^c | t_f | $V_{DD} = 50\text{ V}, R_L = 50\text{ }\Omega, I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 5\text{ }\Omega$ | | N-Ch | - | 17 | 30 |
| | | $V_{DD} = -50\text{ V}, R_L = 50\text{ }\Omega, I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 5\text{ }\Omega$ | | P-Ch | - | 15 | 25 |



| SPECIFICATIONS (T _C = 25 °C, unless otherwise noted) | | | | | | | |
|--|-----------------|-----------------------|------|------|-------|------|---|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT | |
| Source-Drain Diode Ratings and Characteristics ^b | | | | | | | |
| Pulsed Current ^a | I _{SM} | | N-Ch | - | - | 40 | A |
| | | | P-Ch | - | - | -21 | |
| Forward Voltage | V _{SD} | I _S = 6 A | N-Ch | - | 0.89 | 1.2 | V |
| | | I _S = -6 A | P-Ch | - | -0.89 | -1.2 | |

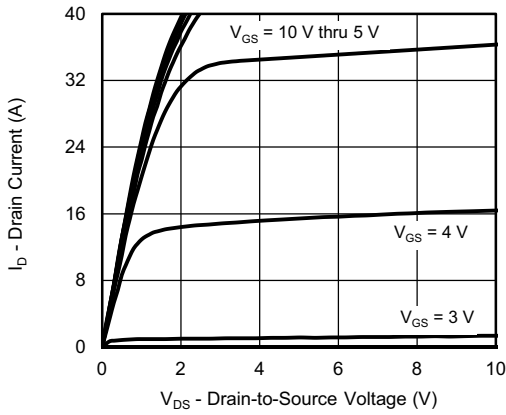
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

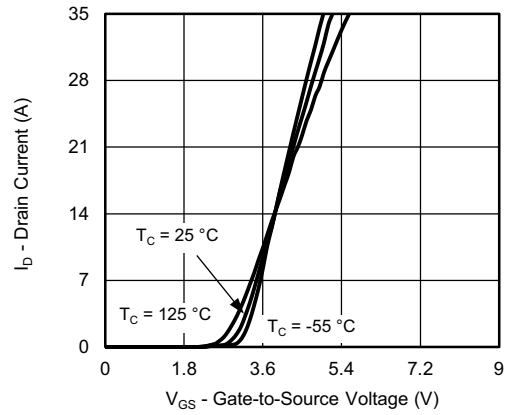
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



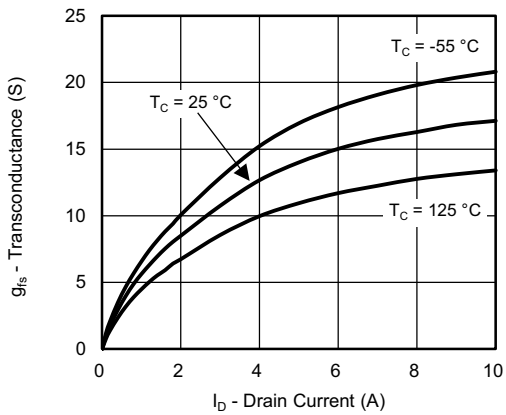
N-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



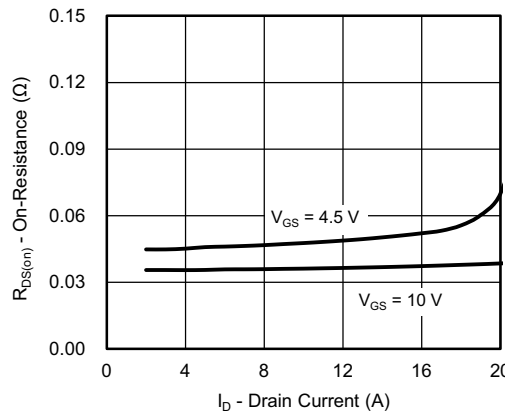
Output Characteristics



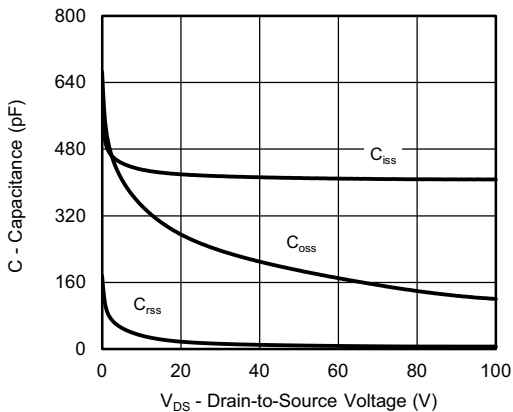
Transfer Characteristics



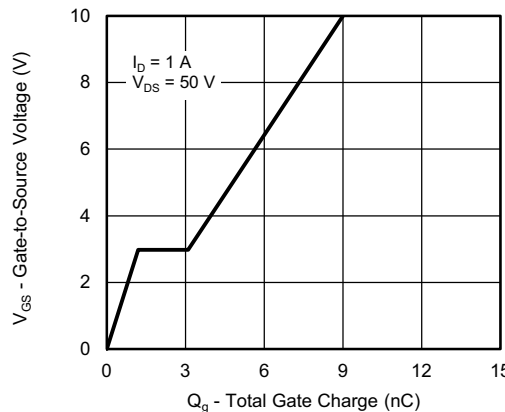
Transconductance



On-Resistance vs. Drain Current



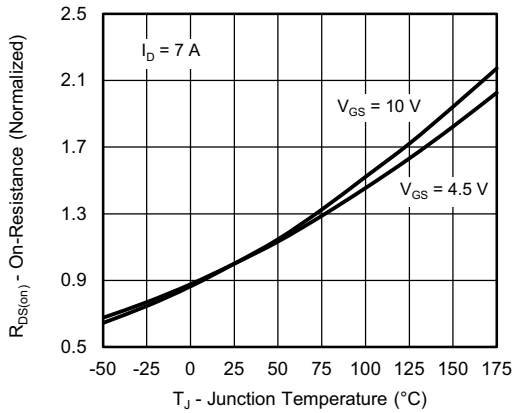
Capacitance



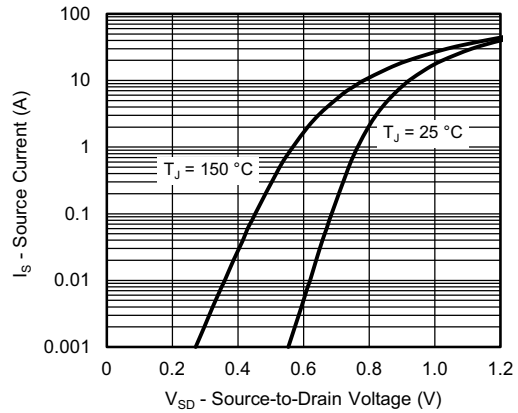
Gate Charge



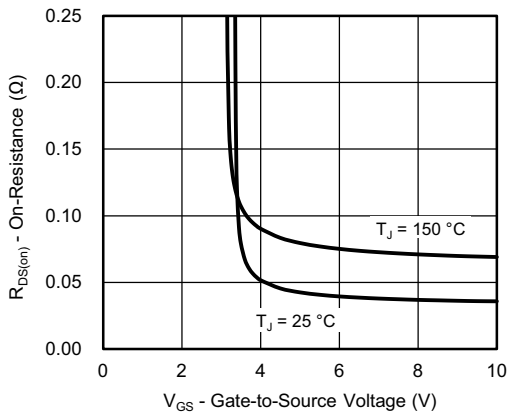
N-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



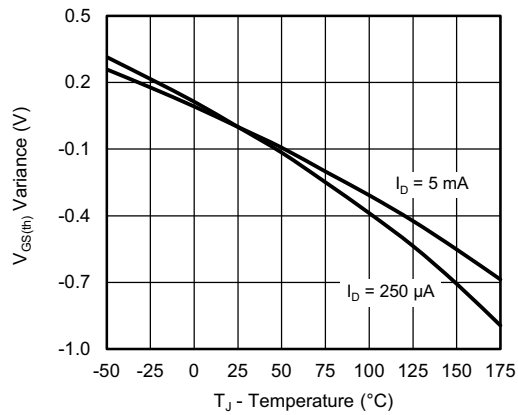
On-Resistance vs. Junction Temperature



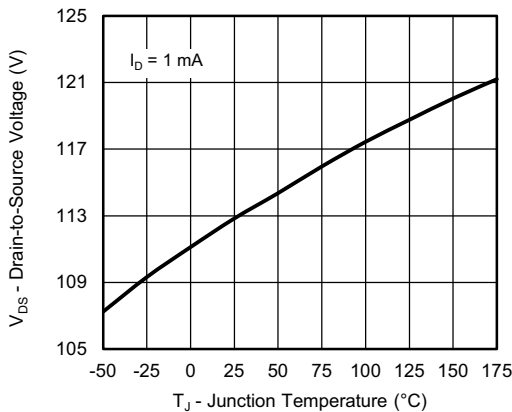
Source Drain Diode Forward Voltage



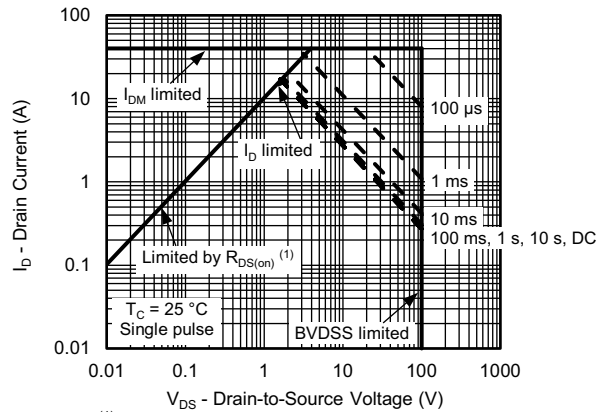
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

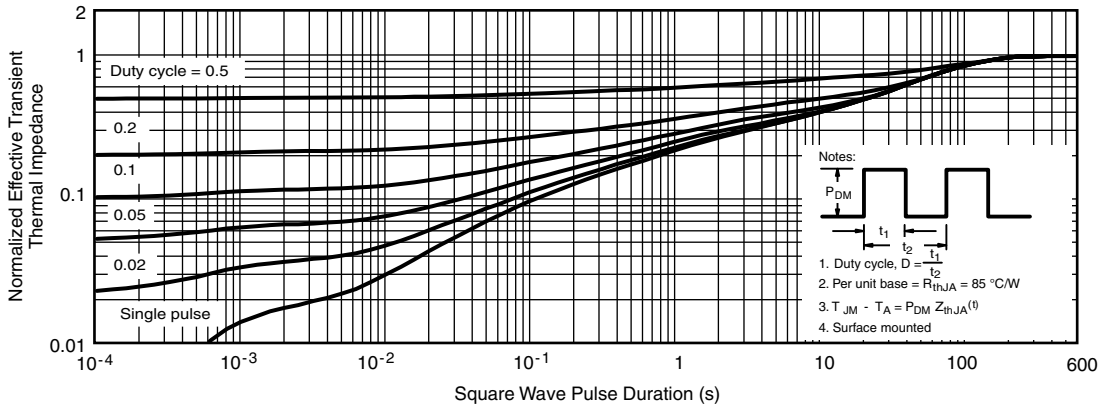


⁽¹⁾ $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

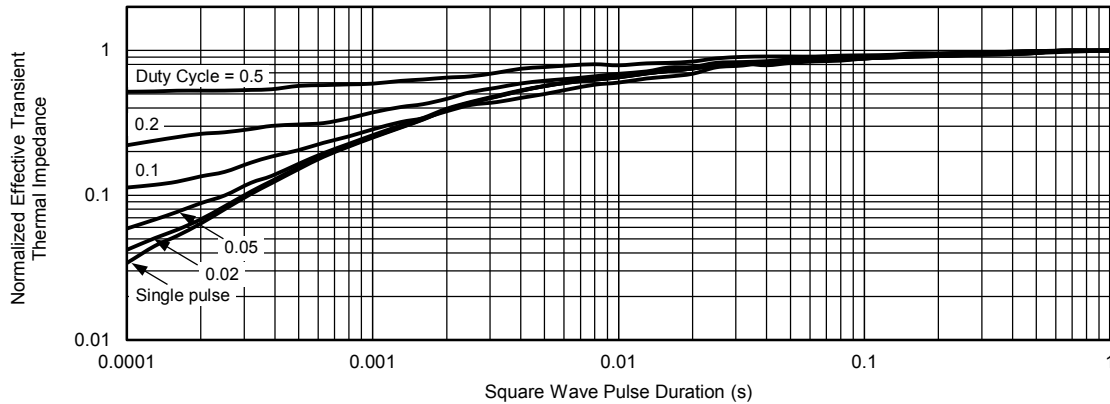
Safe Operating Area



N-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

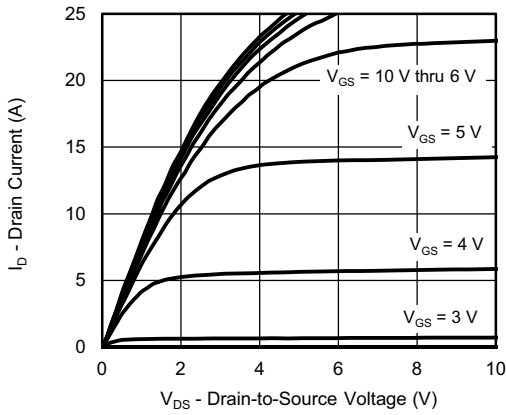


Normalized Thermal Transient Impedance, Junction-to-Case

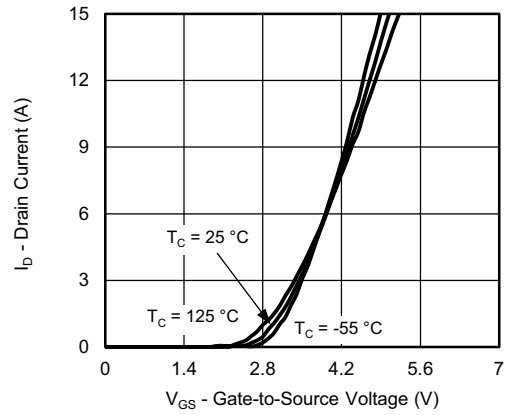
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

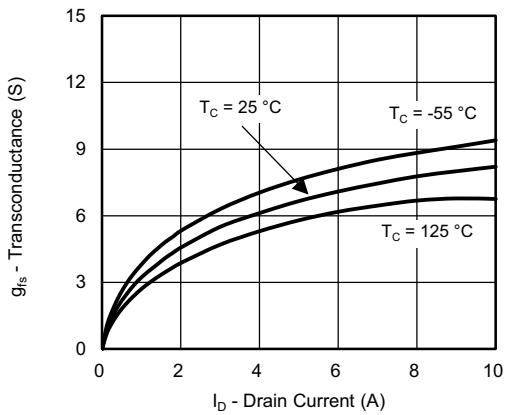
P-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



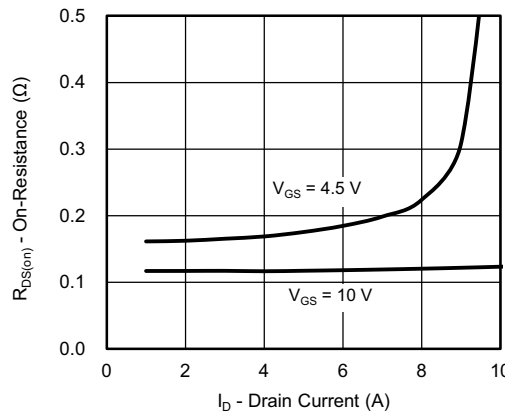
Output Characteristics



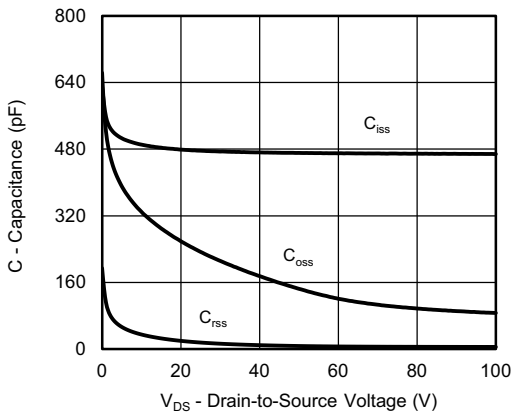
Transfer Characteristics



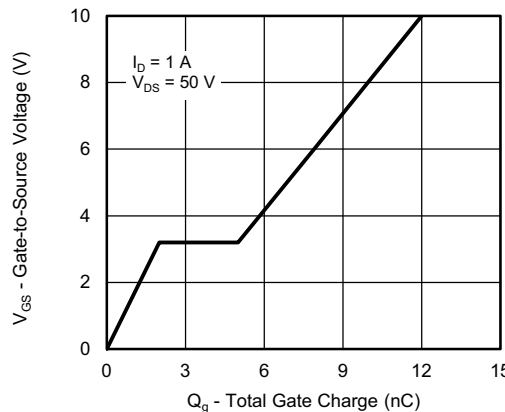
Transconductance



On-Resistance vs. Drain Current



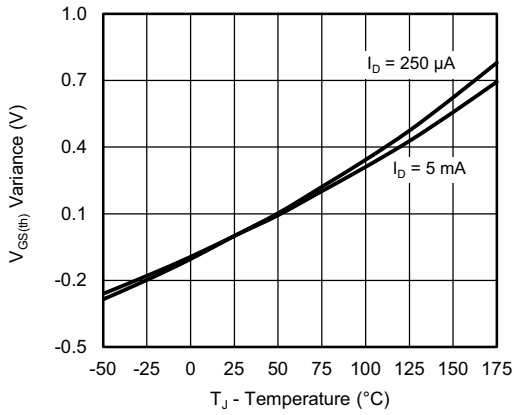
Capacitance



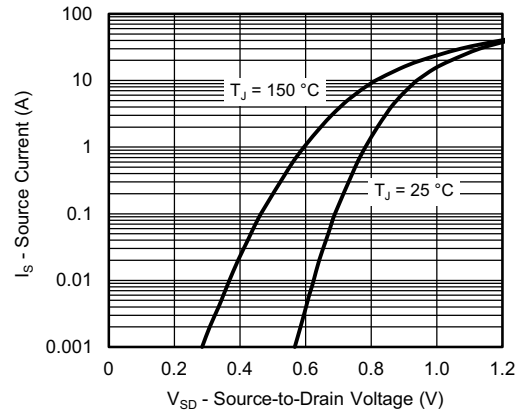
Gate Charge



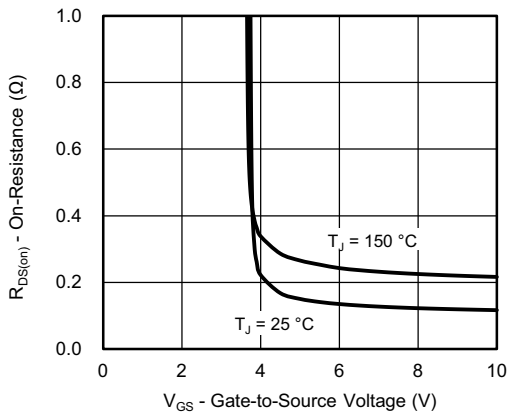
P-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



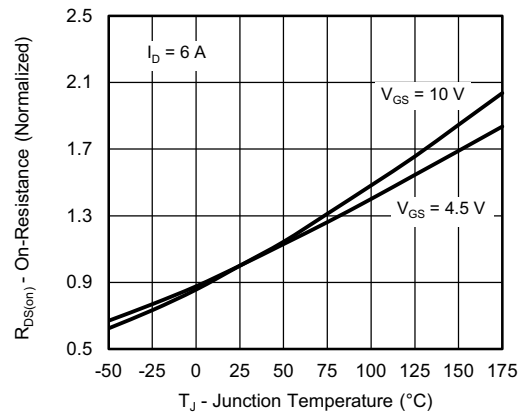
Threshold Voltage



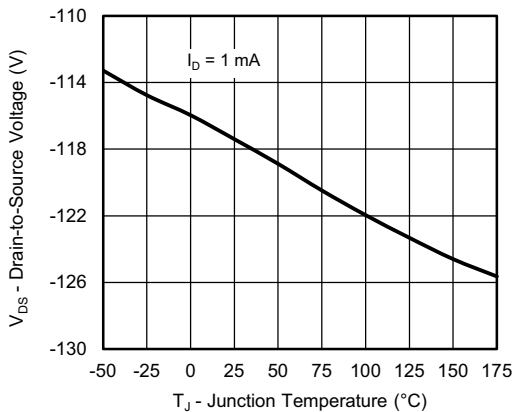
Source Drain Diode Forward Voltage



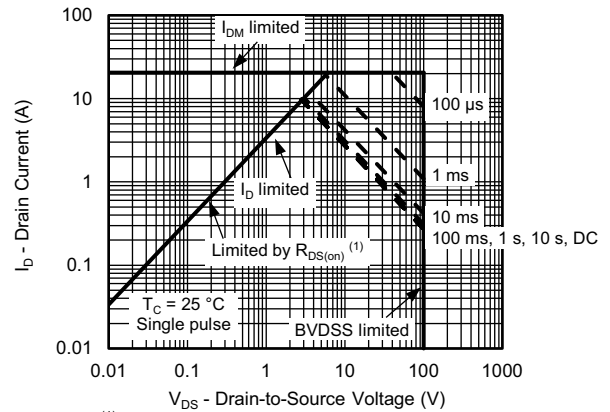
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature



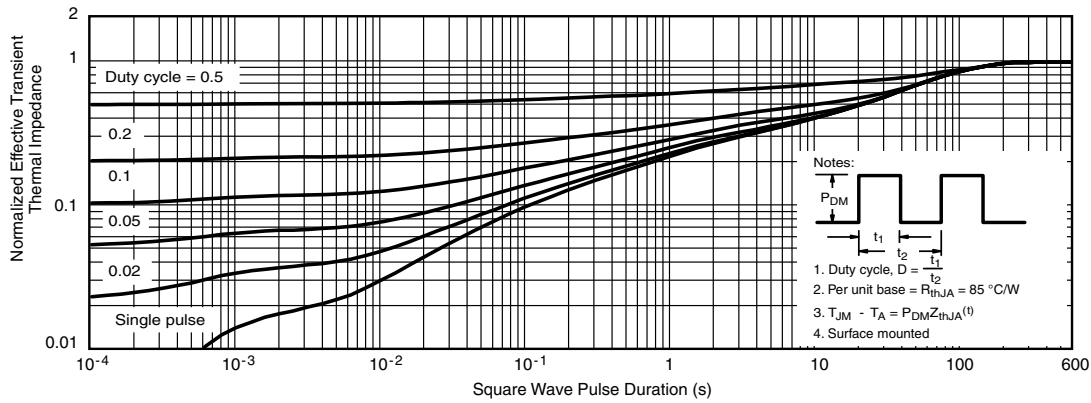
Drain Source Breakdown vs. Junction Temperature



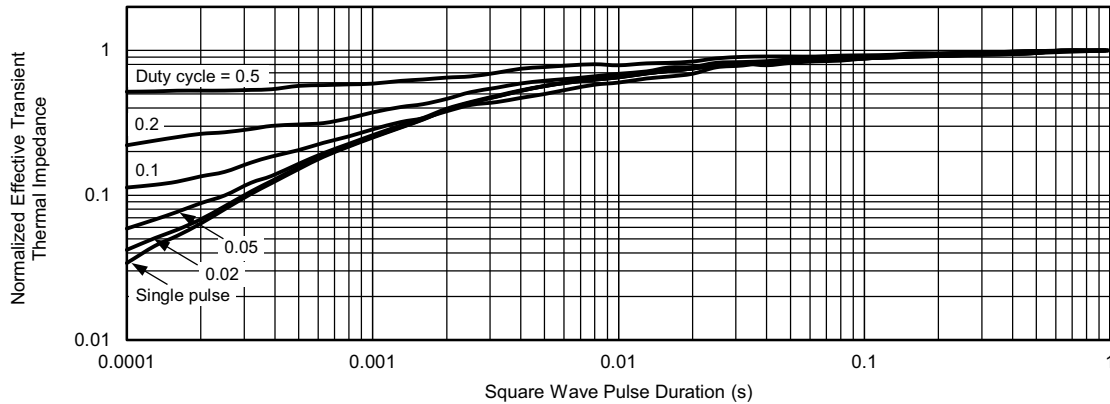
⁽¹⁾ $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

P-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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